

Si Micro-Holes

1 μm in diameter holes with 1.5 μm thick SiO₂ as etch mask

Bosch Process

Dep. Step

- Pressure: 15 mTorr
- C₄F₈: 120 sccm
- Coil power: 600W
- Platen power: 0W
- Time: 5 second

Etch Step

- Pressure: 15 mTorr
- SF₆: 130 sccm
- O₂: 13 sccm
- Coil power: 600W
- Platen power: 12W
- Time: 5 second

Results

- Etch rate: 0.4 μm /min
- Profile: 88°
- Selectivity: 20:1

